

**“AMENDMENT TO CLAIMS”**

1. (currently amended) A semiconductor device assembly comprising:  
a solder mask over a substrate;  
a die;  
conductive paths connecting contacts on said die with contacts in said substrate; and  
a partially-cured adhesive layer between said die and said solder mask, wherein said partially-cured adhesive layer ~~remains voidless after outgassing from said solder mask and~~ is partially cured at a temperature below about 100°C, ~~and~~  
~~an encapsulant molded over the die.~~
2. (currently amended) The semiconductor device assembly of claim 1, wherein said partially-cured adhesive layer is at least fifty percent cured at a temperature below about 100°C.
3. (currently amended) The semiconductor device assembly of claim 1, further comprising an encapsulant molded over the die, whereby ~~wherein~~ said partially-cured adhesive layer is ~~fully~~ cured at a temperature above about 100°.
4. (currently amended) The semiconductor device assembly of claim 1, wherein said partially-cured adhesive layer is partially cured at a temperature between about 20°C and about 50°C higher than the glassy temperature of said adhesive layer.
5. (currently amended) The semiconductor device assembly of claim 4, wherein said partially-cured adhesive layer is partially cured at a temperature below about 85°C.
6. (currently amended) The semiconductor device assembly claim 5, wherein said partially-cured adhesive layer comprises a material with a glassy temperature between about 5°C and about 20°C.

7. (currently amended) The semiconductor device assembly of claim 6, wherein said partially-cured adhesive layer comprises bismaleimide.

8. (currently amended) The semiconductor device assembly of claim 7, wherein said partially-cured adhesive layer consists essentially of bismaleimide.

9. (currently amended) The semiconductor device assembly of claim 1, wherein said partially-cured adhesive layer comprises initiators which react at a temperature below about 100°C.

10. (canceled)

11. (currently amended) The semiconductor device assembly of claim 1 ~~10~~, wherein said contacts are substantially free of contaminants outgassed from said solder mask.

12. (currently amended) A semiconductor device assembly comprising:  
a solder mask on a substrate;

a die;

electrical contacts on said ~~solder mask~~ substrate and said die, each said contact on said die being wire bonded to a respective said contact on said substrate ~~mask~~, said electrical contacts being devoid of contamination caused by outgassing from said solder mask; and

a partially-cured ~~an~~ adhesive layer affixing said die to said solder mask, ~~said adhesive layer being partially-cured~~ said adhesive layer having been subjected to partial curing at a temperature below about 100°C and at a temperature between about 20°C and about 50°C higher than a glassy temperature of said adhesive layer; ~~and~~  
~~an encapsulant molded over the die.~~

13. (canceled)

14. (currently amended) The semiconductor device assembly of claim ~~13~~ 12, wherein said partially-cured adhesive layer is at least fifty percent cured at a temperature below about 100°C.

15. (currently amended) The semiconductor device assembly of claim 12, wherein said partially-cured adhesive layer is cured at a temperature below about 85°C.

16. (currently amended) The semiconductor device assembly of claim 15, wherein said partially-cured adhesive layer comprises a material with a glassy temperature between about 5°C and about 20°C.

17. (currently amended) The semiconductor device assembly of claim 16, wherein said partially-cured adhesive layer comprises bismaleimide.

18. (currently amended) The semiconductor device assembly of claim 17, wherein said partially-cured adhesive layer consists essentially of bismaleimide.

19. (currently amended) The semiconductor device assembly of claim 12, wherein said partially-cured adhesive layer comprises initiators which react at a temperature below about 100°C.

20. (currently amended) The semiconductor device assembly of claim 12, wherein said contacts remain relatively free of contaminants released by outgassing from the solder mask during a cure process.

Claims 21-30 (canceled)

31. (currently amended) The semiconductor device assembly of claim 1, wherein said partially-cured adhesive layer is partially cured at a temperature below about 100°C.

32. (currently amended) The semiconductor device assembly of claim 12, wherein said partially-cured adhesive layer is partially cured at a temperature between about 20°C and about 50°C higher than a glassy temperature of said adhesive layer and said curing temperature is below about 100°C.

33. (new) The semiconductor device assembly of claim 1, wherein the partially-cured adhesive layer is 50% cured.

34. (new) The semiconductor device assembly of claim 1, wherein the partially-cured adhesive layer includes a resin bismaleimide.

35. (new) The semiconductor device assemblage of claim 12, wherein the partially-cured adhesive layer is 50% cured.

36. (new) The semiconductor device assemblage of claim 12, wherein the partially-cured adhesive layer includes a resin bismaleimide.